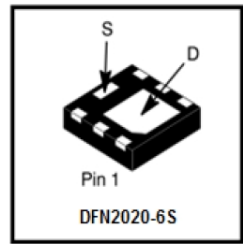


LN3408DT2AG

N-Channel 30V (D-S) MOSFET

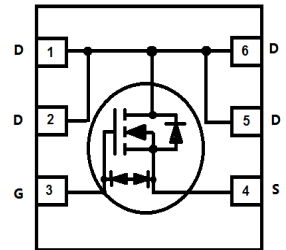
1. FEATURES

- Low RDS(on) trench technology
- Fast Switching Speed
- Low thermal impedance
- We declare that the material of product are Halogen Free and compliance with RoHS requirements.



2. APPLICATIONS

- DC-DC Converter circuit
- Small Signal Switch
- Load Switch



3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LN3408DT2AG	N8S	4000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C unless otherwise stated)

Parameter	Symbol	Limits	Unit	
Drain-to-Source Voltage	VDSS	30	V	
Gate-to-Source Voltage	VGS	±8	V	
Avalanche Current	IAS	20	A	
Avalanche energy L=0.1mH	EAS	20	mJ	
Continuous Drain Current(Note 1)	ID	TA =25°C	10	A
		TA =70°C	8	A
Pulsed Drain Current (Note 2)	IDM	40	A	
Maximum Power Dissipation(Note 1)	PD	TA =25°C	2	W
		TA =70°C	1.3	W
Operating Junction and Storage Temperature Range	TJ/Tstg	-55 ~+150	°C	

5. THERMAL CHARACTERISTICS

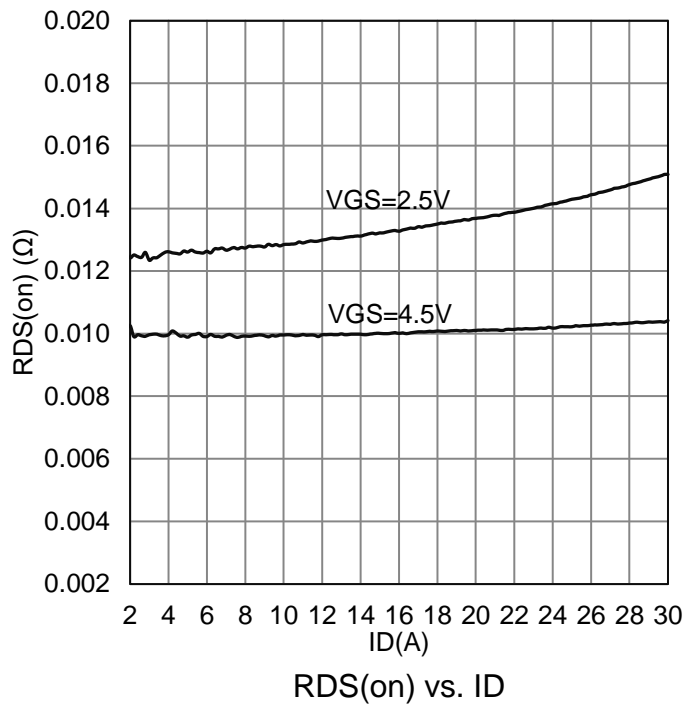
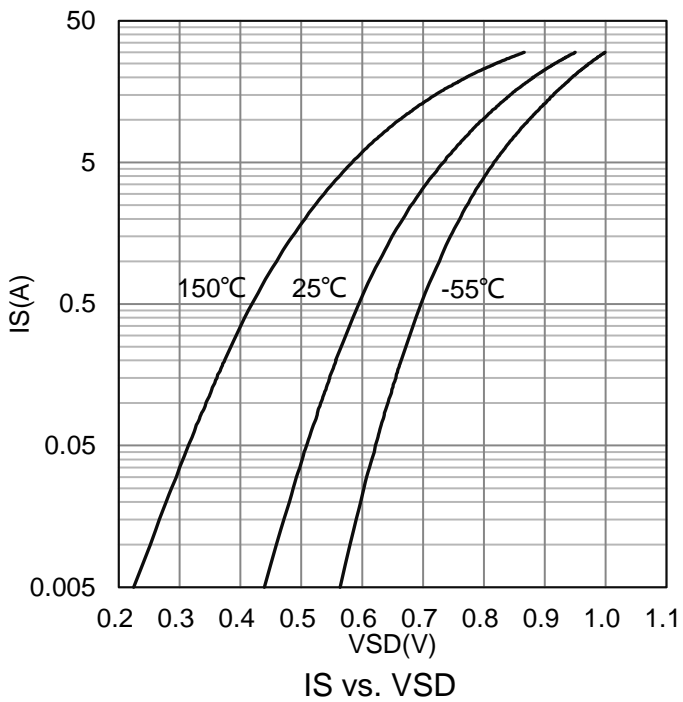
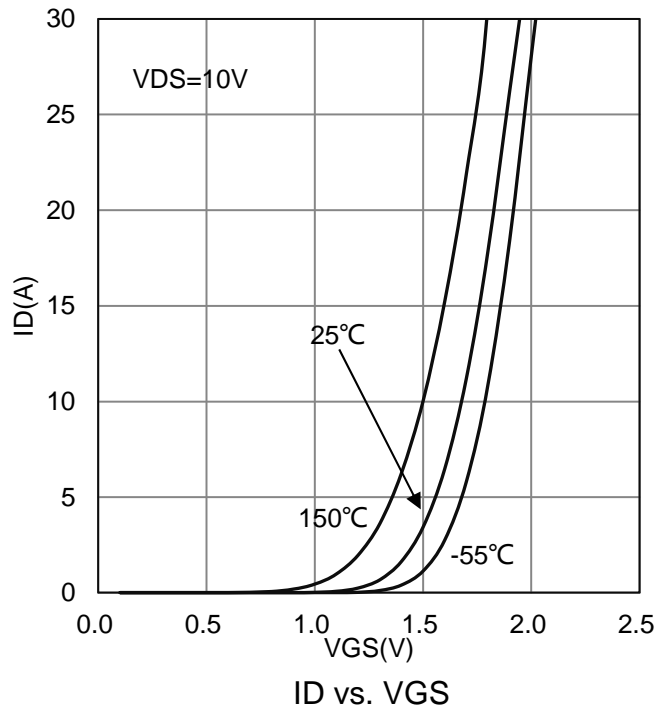
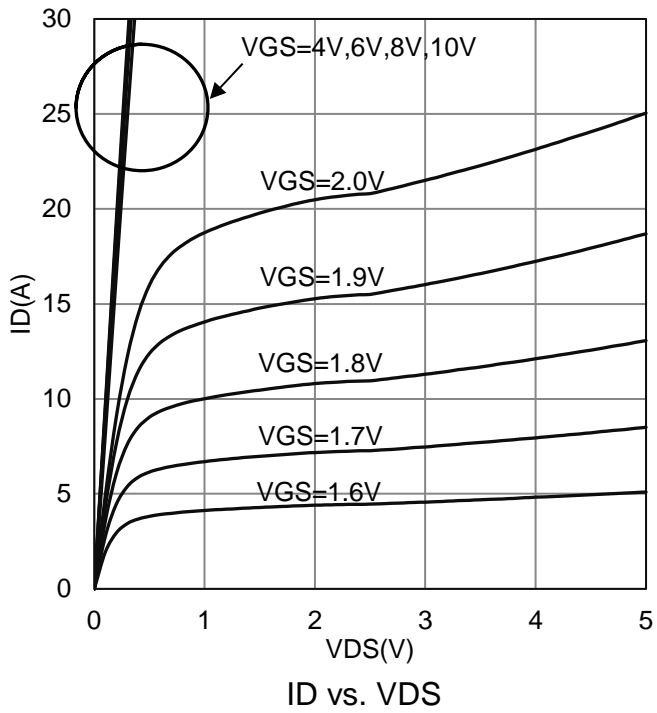
Parameter	Symbol	Limits	Unit
Maximum Junction-to-Ambient(Note 1)	RθJA	62.5	°C/W
Maximum Junction-to-Ambient(Note 3)	RθJA	141	

- 1.Surface mounted on "1.5 x 1.5" FR4 board using 1 sq in pad, 2 oz Cu.
- 2.Pulse width limited by maximum junction temperature.
- 3.Surface-mounted on FR4 board using the minimum recommended pad size.

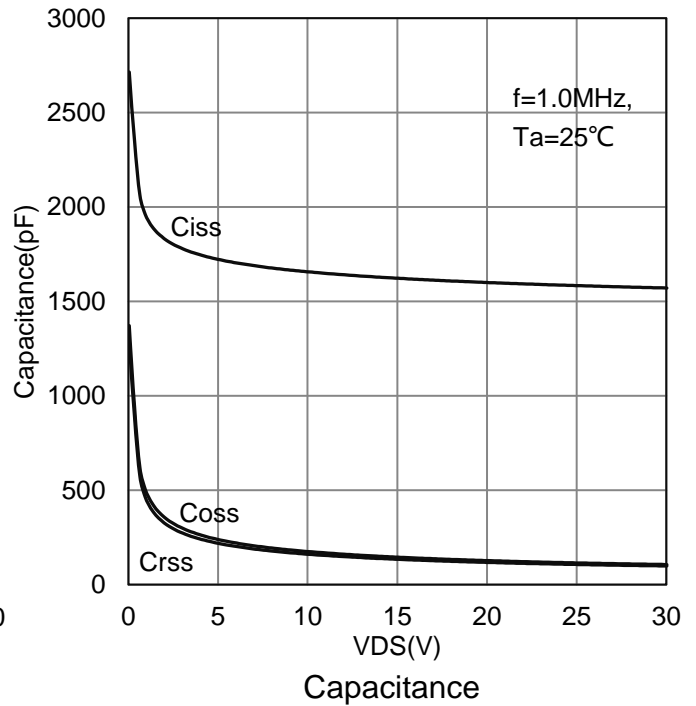
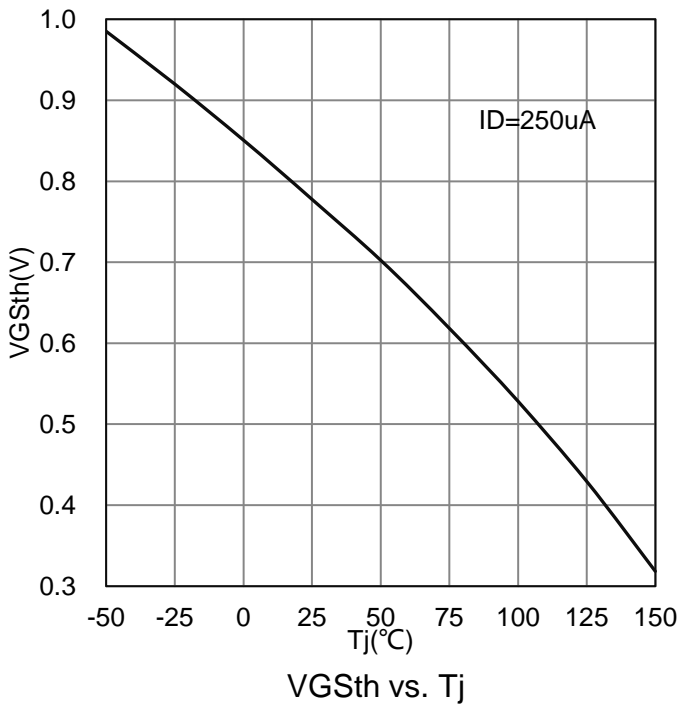
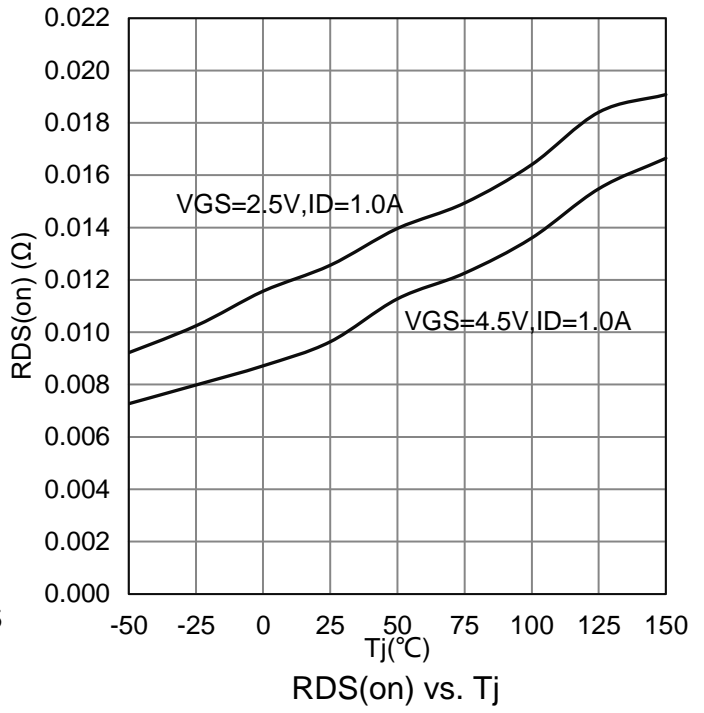
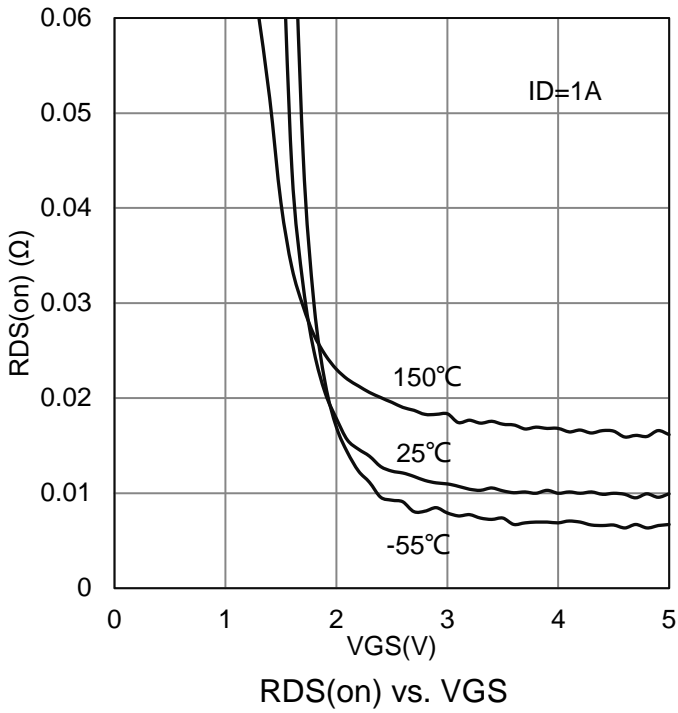
6. ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain-Source Breakdown Voltage (VGS = 0V, ID = 250μA)	V(BR)DSS	30	-	-	V
Gate-Source Threshold Voltage (VDS = VGS, ID = 250μA)	VGS(th)	0.45	-	1	V
Gate Leakage Current (VDS = 0V, VGS = ±8V)	IGSS	-	-	±10	uA
Zero Gate Voltage Drain Current (VDS = 30 V, VGS = 0 V)	IDSS	-	-	1	uA
Drain-Source On-Resistance (VGS = 4.5V, ID = 8A) (VGS = 2.5V, ID = 6.8A) (VGS = 1.8V, ID = 4A)	RDS(ON)	-	-	16 20 39	mΩ
Diode Forward Voltage (IS = 1 A, VGS = 0 V)	VSD	-	-	1.2	V
Dynamic					
Total Gate Charge	Qg (VDS = 15 V, VGS = 4.5 V, ID = 8 A)	Qg	-	20	nC
Gate-Source Charge		Qgs	-	3.8	
Gate-Drain Charge		Qgd	-	5.3	
Input Capacitance	Ciss (VDS = 15 V, VGS = 0 V, f = 1MHz)	Ciss	-	1472	pF
Output Capacitance		Coss	-	146	
Reverse Transfer Capacitance		Crss	-	134	
Turn-On Delay Time	td(on) tr td(off) tf (VDS = 15 V, ID = 8 A, VGS = 4.5 V, RL = 1.9 Ω, RG = 6 Ω)	td(on)	-	12.5	ns
Turn-On Rise Time		tr	-	23.5	
Turn-Off Delay Time		td(off)	-	70	
Turn-Off Fall Time		tf	-	36	

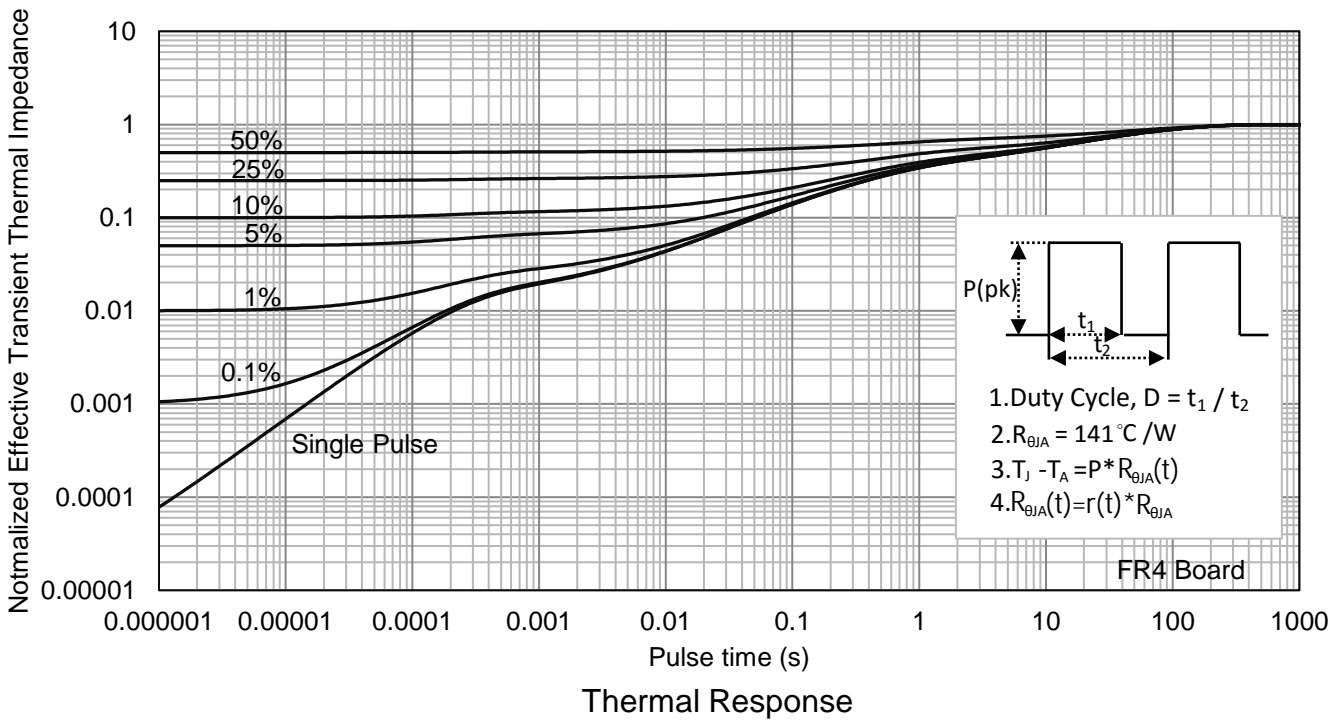
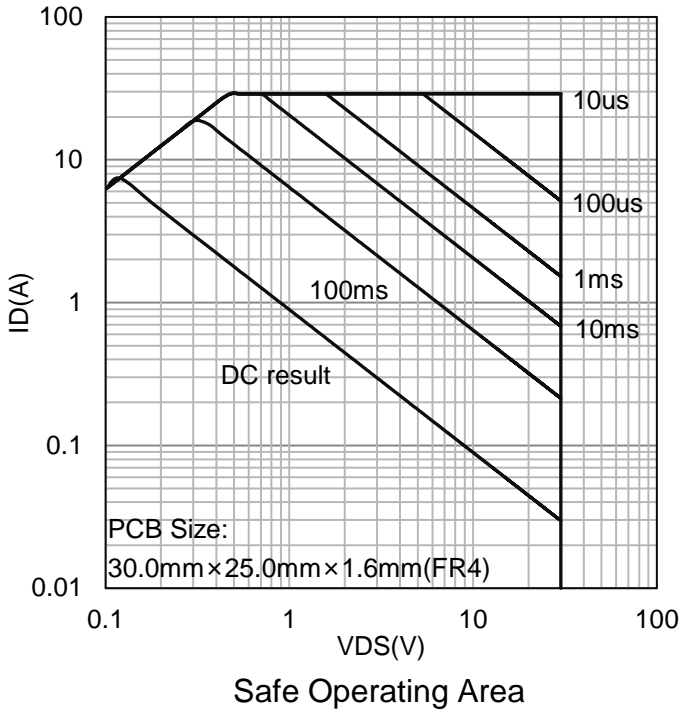
7. ELECTRICAL CHARACTERISTICS CURVES



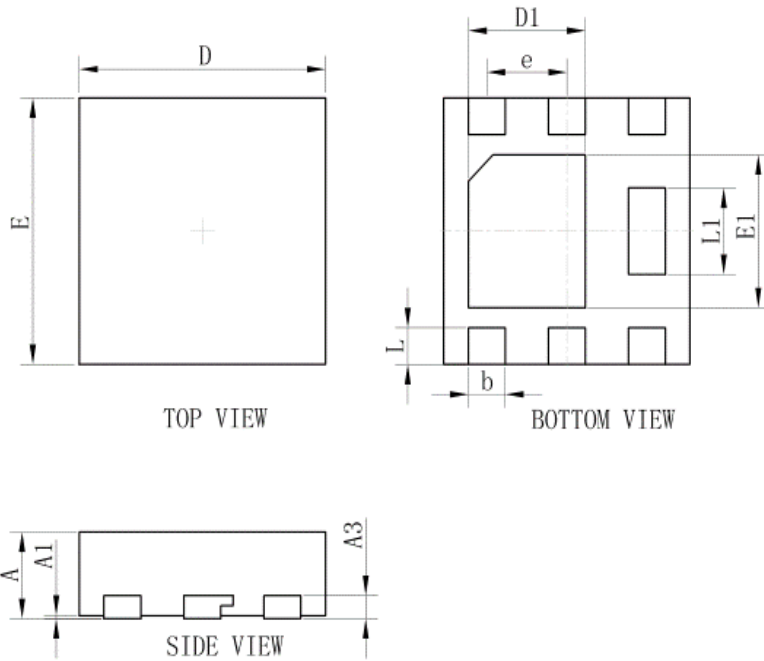
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

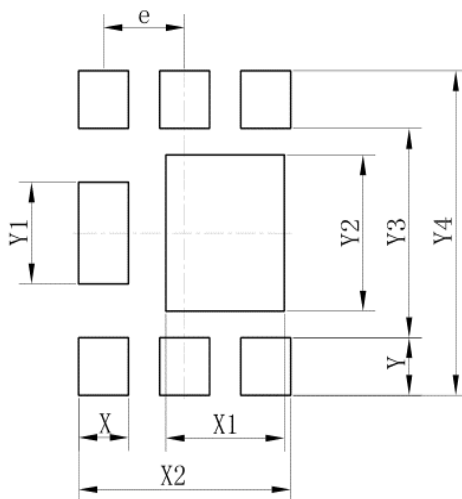


8. OUTLINE AND DIMENSIONS



DFN2020-6S			
DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.01	0.03	0.05
b	0.25	0.30	0.35
D	1.95	2.00	2.05
E	1.95	2.00	2.05
e	0.65TYP.		
L	0.23	0.28	0.33
L1	0.60	0.65	0.70
D1	0.90	0.95	1.00
E1	1.10	1.15	1.20
A3	0.152REF		
All Dimensions in mm			

9. SOLDERING FOOTPRINT



DFN2020-6S	
Dim	(mm)
X	0.40
X1	0.95
X2	1.70
e	0.65
Y	0.43
Y1	0.75
Y2	1.15
Y3	1.54
Y4	2.39

DISCLAIMER

- Before you use our Products, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)